

8550 (1.5A)

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications.
Especially suitable for AF-driver stages
and low power output stages.



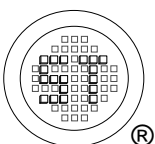
1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	40	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	25	V
Emitter Base Voltage	$-V_{\text{EBO}}$	6	V
Collector Current	$-I_{\text{C}}$	1.5	A
Power Dissipation	P_{tot}	1	W
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 5\text{ mA}$	h_{FE}	45	-	-	-
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 100\text{ mA}$	h_{FE}	120	-	200	-
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 800\text{ mA}$	h_{FE}	160	-	300	-
Current Gain Group C D	h_{FE}	40	-	-	-
Collector Base Cutoff Current	$-I_{\text{CBO}}$	-	-	100	nA
at $-V_{\text{CB}} = 35\text{ V}$					
Emitter Base Cutoff Current	$-I_{\text{EBO}}$	-	-	100	nA
at $-V_{\text{BE}} = 6\text{ V}$					
Collector Base Breakdown Voltage	$-V_{(\text{BR})\text{CBO}}$	40	-	-	V
at $-I_{\text{C}} = 100\text{ }\mu\text{A}$					
Collector Emitter Breakdown Voltage	$-V_{(\text{BR})\text{CEO}}$	25	-	-	V
at $-I_{\text{C}} = 2\text{ mA}$					
Emitter Base Breakdown Voltage	$-V_{(\text{BR})\text{EBO}}$	6	-	-	V
at $-I_{\text{E}} = 100\text{ }\mu\text{A}$					
Collector Emitter Saturation Voltage	$-V_{\text{CE(sat)}}$	-	-	0.5	V
at $-I_{\text{C}} = 800\text{ mA}$, $-I_{\text{B}} = 80\text{ mA}$					
Base Emitter Saturation Voltage	$-V_{\text{BE(sat)}}$	-	-	1.2	V
at $-I_{\text{C}} = 800\text{ mA}$, $-I_{\text{B}} = 80\text{ mA}$					
Base Emitter Voltage	$-V_{\text{BE}}$	-	-	1	V
at $-I_{\text{C}} = 10\text{ mA}$, $-V_{\text{CE}} = 1\text{ V}$					
Gain Bandwidth Product	f_{T}	120	-	-	MHz
at $-V_{\text{CE}} = 10\text{ V}$, $-I_{\text{C}} = 50\text{ mA}$					
Collector Base Capacitance	C_{ob}	-	15	-	pF
at $-V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$					



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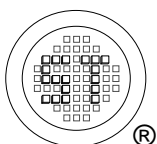
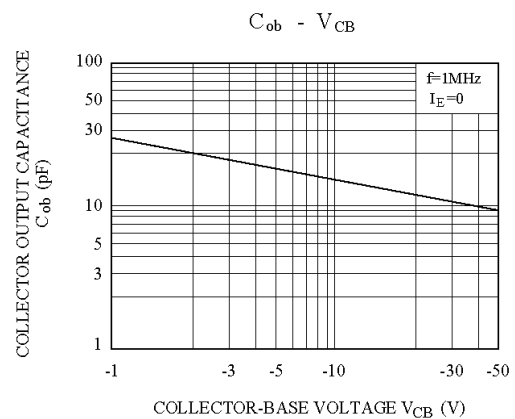
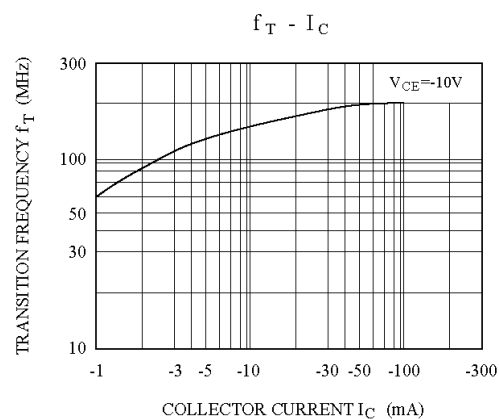
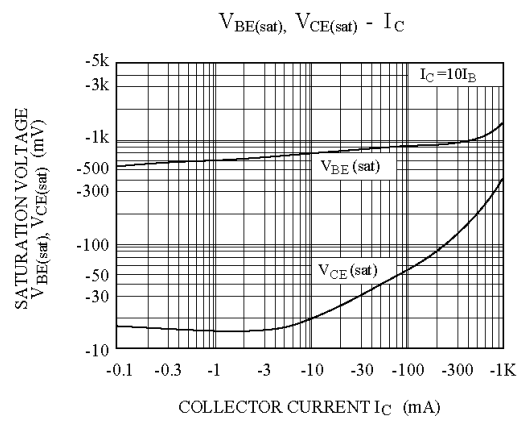
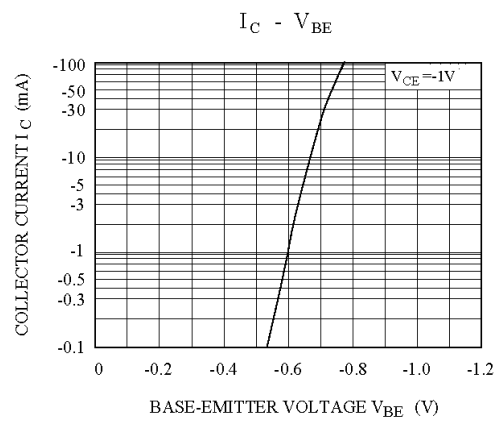
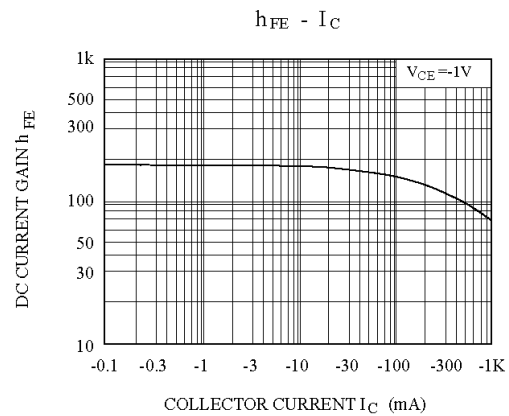
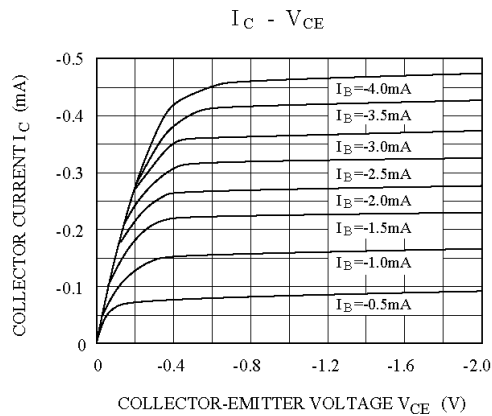


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